

# 2SK3288

Silicon N Channel MOS FET  
High Speed Switching

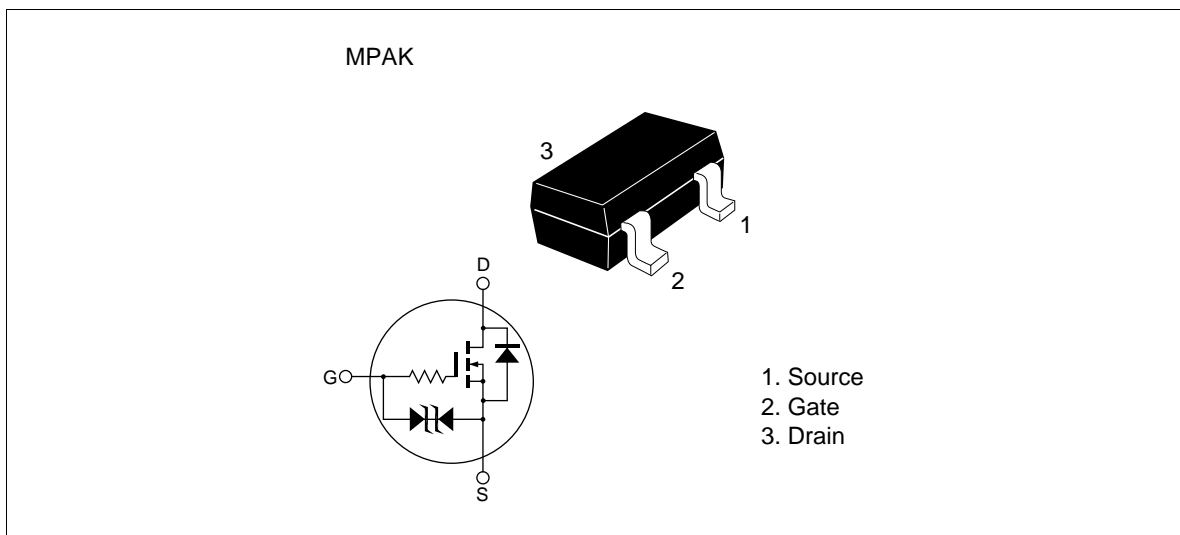
# HITACHI

ADE-208-803 (Z)  
1st.Edition.  
June 1999

## Features

- Low on-resistance  
 $R_{DS} = 2.7 \Omega$  typ. ( $V_{GS} = 10 \text{ V}$ ,  $I_D = 50 \text{ mA}$ )  
 $R_{DS} = 4.7 \Omega$  typ. ( $V_{GS} = 4 \text{ V}$ ,  $I_D = 20 \text{ mA}$ )
- 4 V gate drive device.
- Small package (MPAK)

## Outline



## 2SK3288

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	30	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	100	mA
Drain peak current	$I_{D(pulse)}$ <sup>Note 1</sup>	400	mA
Body-drain diode reverse drain current	$I_{DR}$	100	mA
Channel dissipation	Pch <sup>Note 2</sup>	400	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

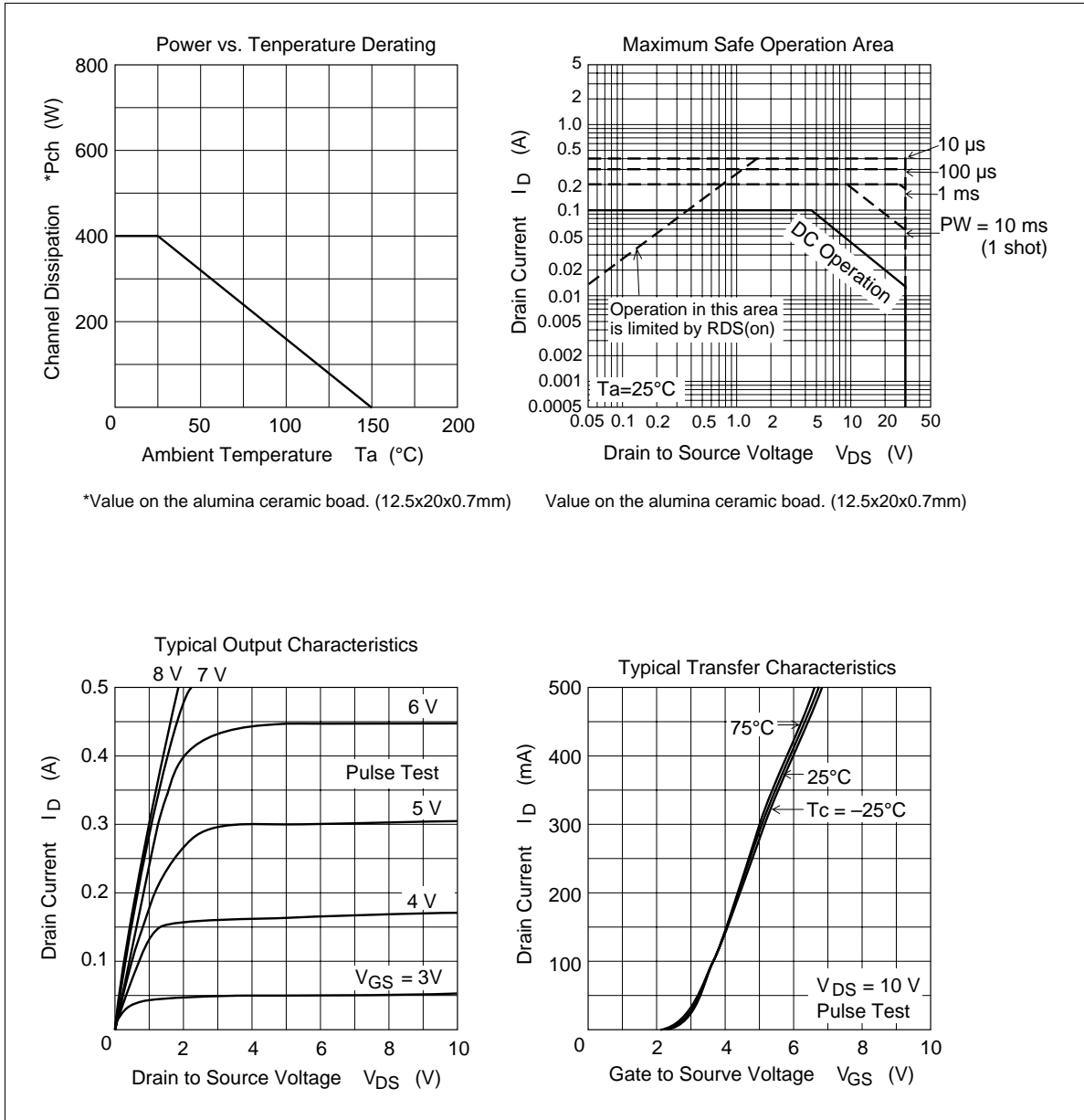
Note: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$   
 2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

### Electrical Characteristics (Ta = 25°C)

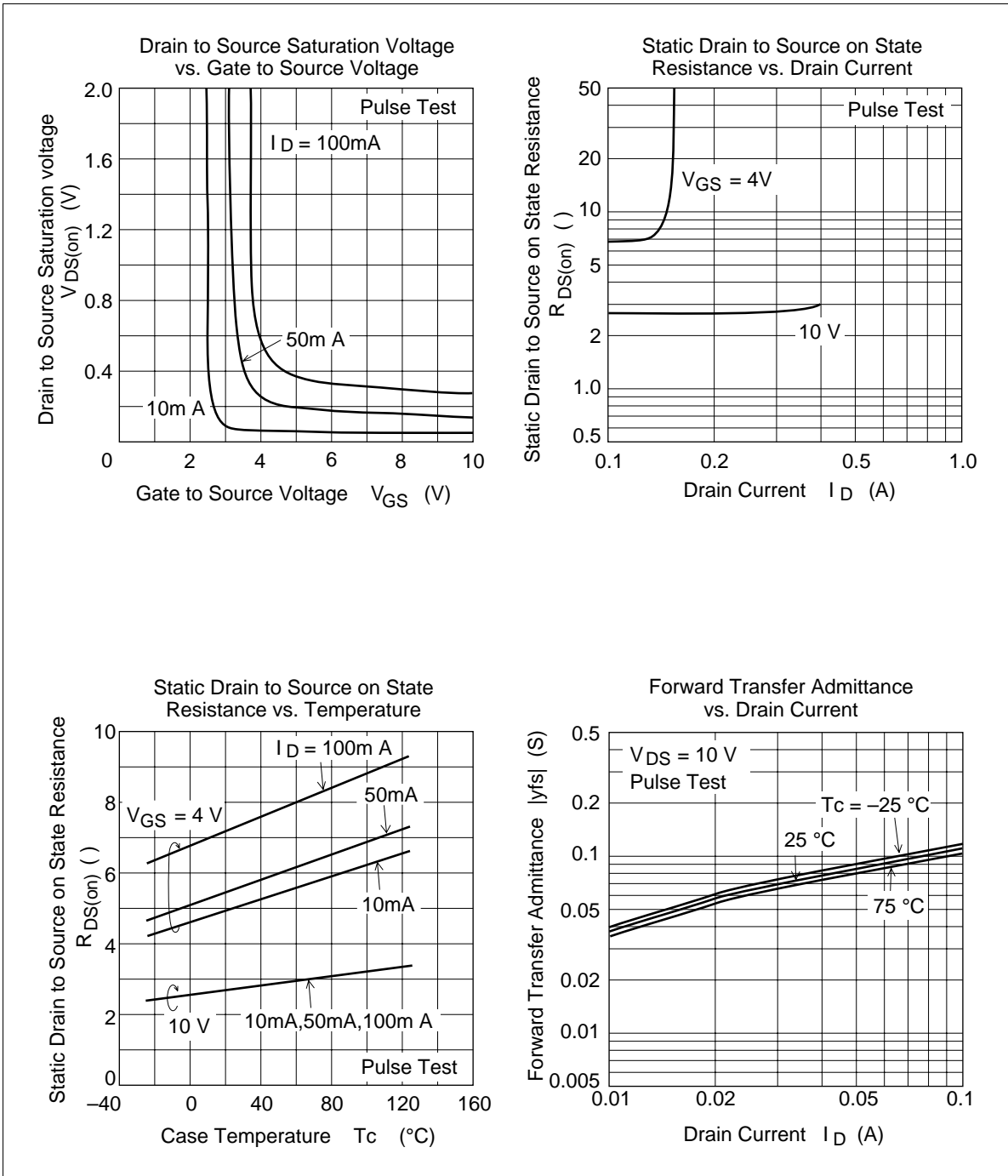
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 5$	$\mu A$	$V_{GS} = \pm 16 V, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 30 V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.3	—	2.3	V	$I_D = 10 \mu A, V_{DS} = 5 V$
Static drain to source on state resistance	$R_{DS(on)}$	—	2.7	3.5	$\Omega$	$I_D = 50 mA, V_{GS} = 10 V$ <sup>Note 3</sup>
	$R_{DS(on)}$	—	4.7	7.0	$\Omega$	$I_D = 20 mA, V_{GS} = 4 V$ <sup>Note 3</sup>
Forward transfer admittance	$ y_{fs} $	55	85	—	mS	$I_D = 50 mA, V_{DS} = 10 V$ <sup>Note 3</sup>
Input capacitance	Ciss	—	3	—	pF	$V_{DS} = 10 V$
Output capacitance	Coss	—	8	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	1	—	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	100	—	ns	$I_D = 50 mA, V_{GS} = 10 V$
Rise time	$t_r$	—	300	—	ns	$R_L = 200 \Omega$
Turn-off delay time	$t_{d(off)}$	—	1100	—	ns	
Fall time	$t_f$	—	900	—	ns	

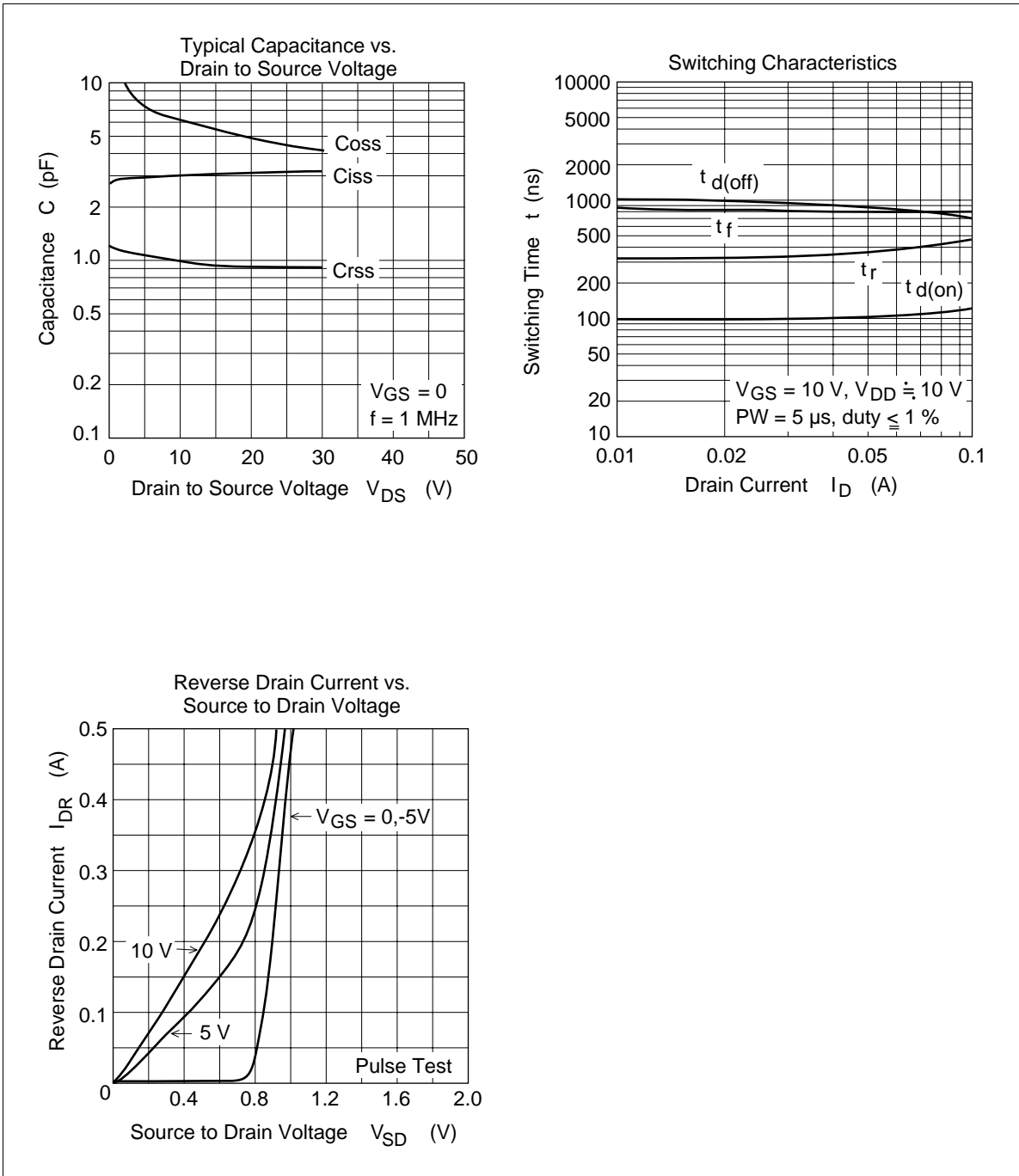
Note: 3. Pulse test  
 4. Marking is EN

Main Characteristics

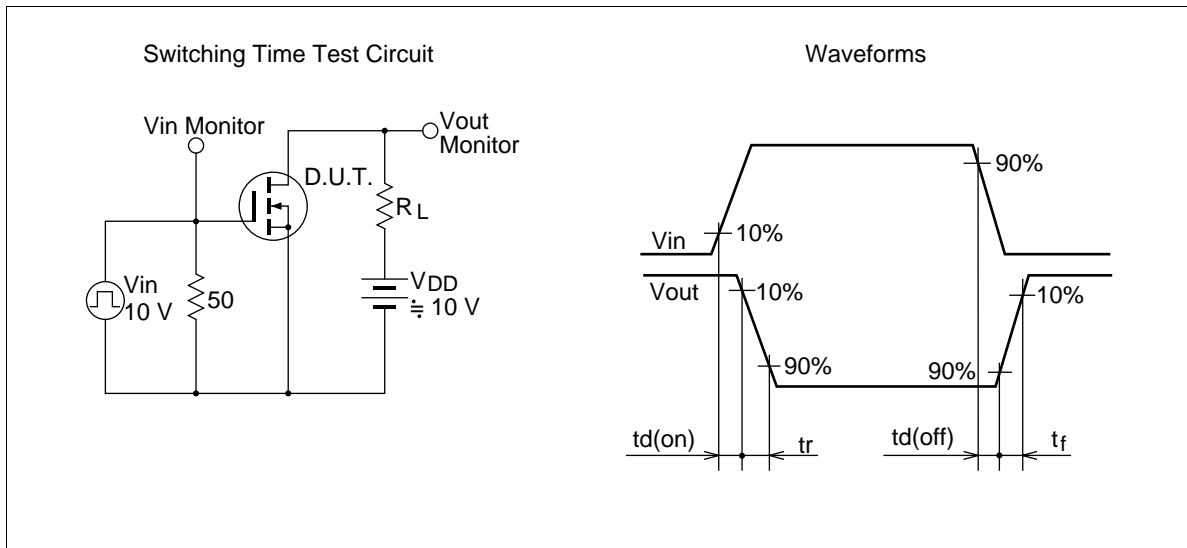


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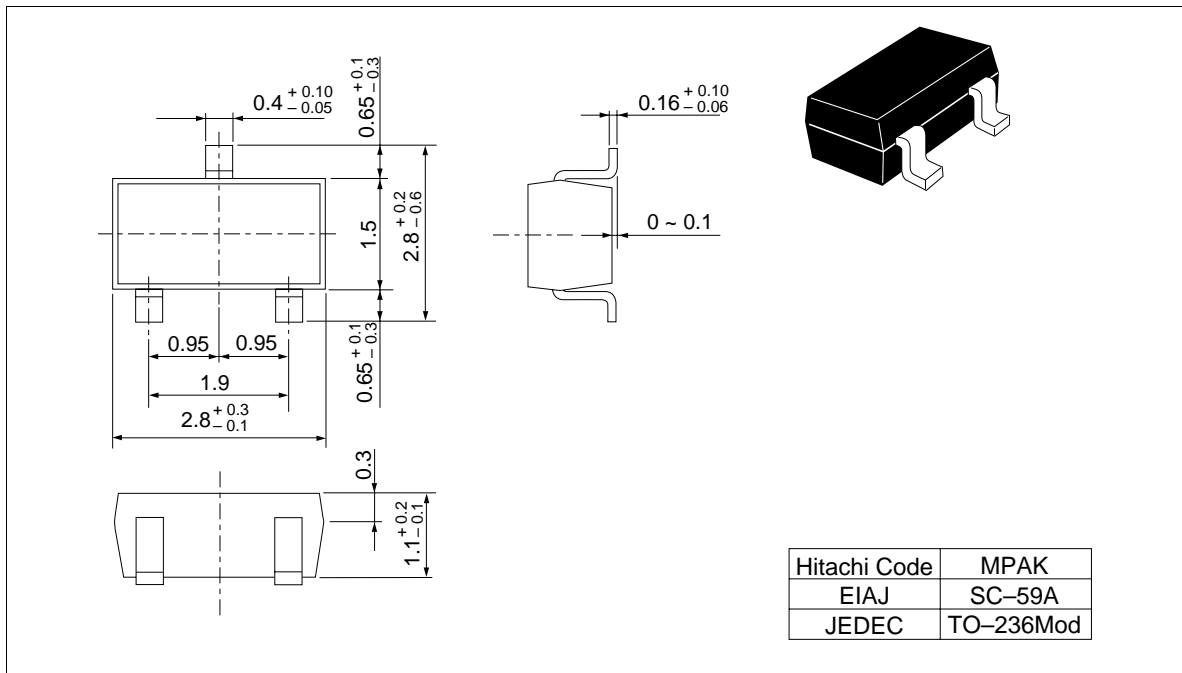


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**Package Dimensions**

Unit: mm



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